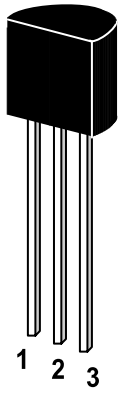
ST 2SC1740

NPN Silicon Epitaxial Planar Transistor
for switching and AF amplifier applications.

The transistor is subdivided into four groups Q, R, S and E. according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25℃)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	60	V
Collector Emitter Voltage	V_{CEO}	50	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	150	mA
Power Dissipation	P_{tot}	300	mW
Junction Temperature	T_j	150	^{O}C
Storage Temperature Range	T_S	-55 to +150	^{O}C

Characteristics at T_{amb}=25 °C

		Symbol	Min.	Typ.	Max.	Unit
DC Current Gain						
at V_{CE}=6V, I_C=1mA	Q	h_{FE}	120	-	270	-
	R	h_{FE}	180	-	390	-
	S	h_{FE}	270	-	560	-
	E	h_{FE}	390	-	820	-
Collector Base Breakdown Voltage at I_C=50μA		$V_{(BR)CBO}$	60	-	-	V
Collector Emitter Breakdown Voltage at I_C=1mA		$V_{(BR)CEO}$	50	-	-	V
Emitter Base Breakdown Voltage at I_E=50μA		$V_{(BR)EBO}$	5	-	-	V
Collector Cutoff Current at V_{CB}=60V		I_{CBO}	-	-	0.1	μA
Emitter Cutoff Current at V_{EB}=5V		I_{EBO}	-	-	0.1	μA
Collector Saturation Voltage at I_C=50mA, I_B=5mA		$V_{CE(sat)}$	-	-	0.4	V
Gain Bandwidth Product at V_{CE}=12V, I_C=2mA		f_T	-	180	-	MHz
Output Capacitance at V_{CB}=12V, f=1MHz		C_{OB}	-	2	3.5	pF